TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

FEATURES

Power dissipation

P_{CM} : 0.5W (Tamb=25°C)

Collector current

I_{CM} : -1.5A

Collector-base Voltage

$V_{(BR)CBO}$: -35 V

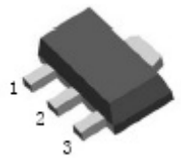
Operating and storage junction temperature range

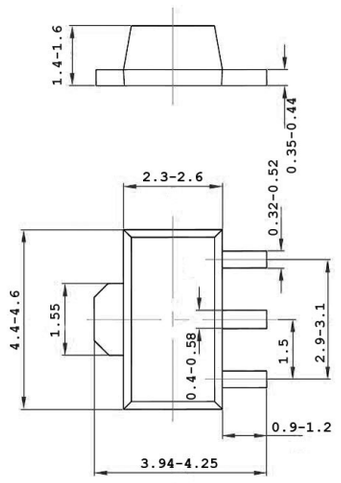
T_J, T_{stg} : -55°C to +150°C

MARKING : HO ,HY

SOT-89

1. BASE
2. COLLECTOR(HEAT SINK)
3. EMITTER





UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-35			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC Current Gain	h_{FE}	V_{CE}=-2V, I_C=-500mA	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.5A, I_B=-30mA			-2.0	V
Base-Emitter Saturation Voltage	V_{BE}	V_{CE}=-2V, I_C=500mA			-1.0	
Transition Frequency	f_T	V_{CE}=-5V, I_C=-50mA	80			MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			50	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

RoHS Pb-free TIP Semiconductor